P-Channel 30-V (D-S) MOSFET

Key Features:

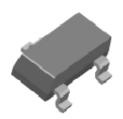
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

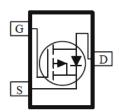
Typical Applications:

- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _D (A)	
-30	112 @ $V_{GS} = -4.5V$	-2.8	
	$172 @ V_{GS} = -2.5V$	-2.3	







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage			V _{DS}	-30	V	
Gate-Source Voltage		V _{GS}	±8	V		
Continuous Drain Correct a		T _A =25°C	ı	-2.8		
Continuous Drain Current ^a	Ī	T _A =70°C	I _D	-2.2	Α	
Pulsed Drain Current ^b		I _{DM}	-10	'		
Continuous Source Current (Diode Conduction) a			I _S	-1.7	Α	
Dower Dissipation a		T _A =25°C	P_{D}	1.3	W	
Power Dissipation ^a		T _A =70°C	ı D	0.8	v v	
Operating Junction and Storage Temperature Range			T_J,T_sta	-55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter			Maximum	Units		
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	100	°C/W		
Maximum Junction-to-Ambient	Steady State		166			

1

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

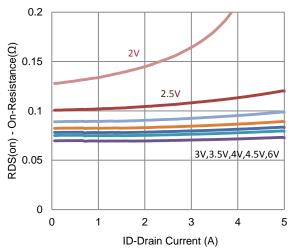
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-0.4			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	ı	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$			-1	uA	
	I _{DSS}	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-25	uA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-4			Α	
Drain-Source On-Resistance ^a	r	$V_{GS} = -4.5 \text{ V}, I_D = -2 \text{ A}$			112	mΩ	
	r _{DS(on)}	$V_{GS} = -2.5 \text{ V}, I_D = -1.6 \text{ A}$			172		
Forward Transconductance ^a	g _{fs}	$V_{DS} = -15 \text{ V}, I_{D} = -2.5 \text{ A}$		11		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = -0.9 \text{ A}, V_{GS} = 0 \text{ V}$		-0.8		V	
Dynamic ^b							
Total Gate Charge	Q_g	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V},$		8.4		nC	
Gate-Source Charge	Q_gs	$I_{DS} = -13 \text{ V}, \text{ V}_{GS} = -4.3 \text{ V},$ $I_{D} = -2 \text{ A}$		1.3			
Gate-Drain Charge	Q_gd	10 - 2 A		2.5			
Turn-On Delay Time	t _{d(on)}			8			
Rise Time	t _r	$V_{DS} = -15 \text{ V}, R_L = 7.5 \Omega, I_D = -2 \text{ A},$		6		ns	
Turn-Off Delay Time	$t_{d(off)}$	V_{GEN} = -4.5 V, R_{GEN} = 6 Ω		29			
Fall Time	t _f			11			
Input Capacitance	C _{iss}			474			
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		52		pF	
Reverse Transfer Capacitance	C_{rss}			48			

Notes

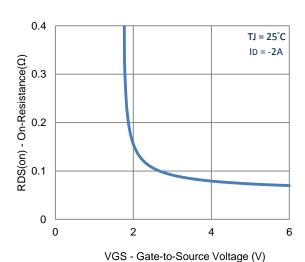
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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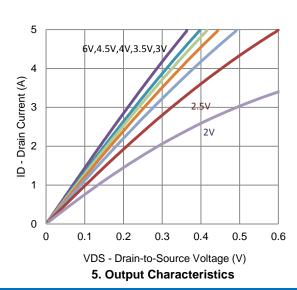
Typical Electrical Characteristics

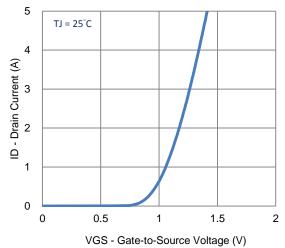


1. On-Resistance vs. Drain Current

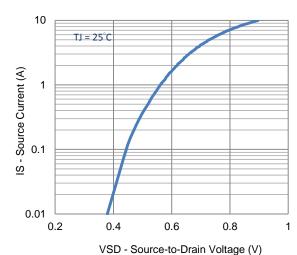


3. On-Resistance vs. Gate-to-Source Voltage

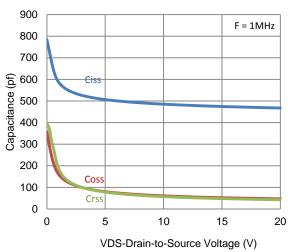




2. Transfer Characteristics

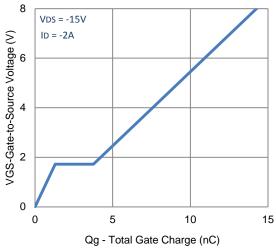


4. Drain-to-Source Forward Voltage

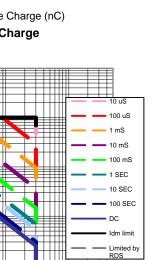


6. Capacitance

Typical Electrical Characteristics



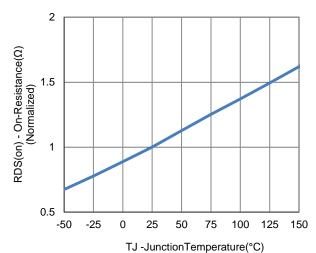




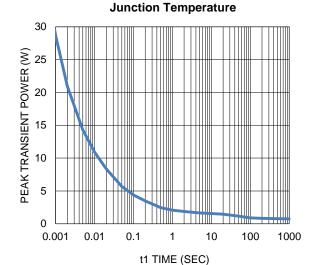
VDS Drain to Source Voltage (V)

10

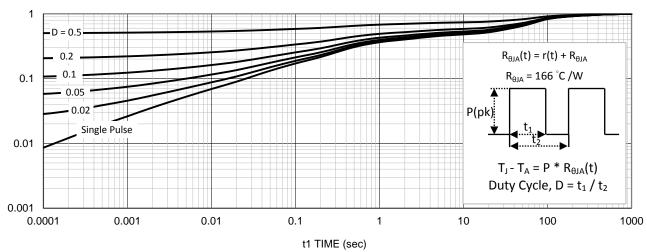
9. Safe Operating Area



8. Normalized On-Resistance Vs



10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

100

10

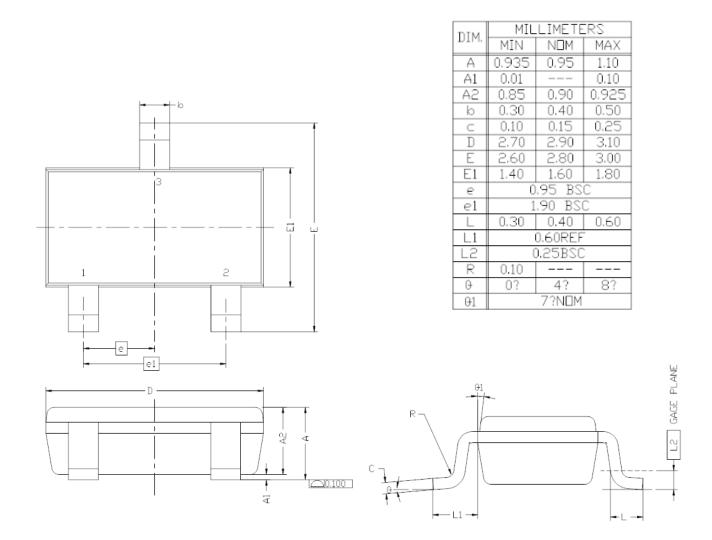
0.1

0.01

0.1

ID Current (A)

Package Information



Note:

- 1. All Dimension Are In mm.
- Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Tie Bar Burrs, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.
- 4. The Package Top May Be Smaller Than The Package Bottom.
- 5. Dimension "B" Does Not Include Dambar Protrusion. Allowable Dambar Protrusion Shall Be 0.08 mm Total In Excess Of "B" Dimension At Maximum Material Condition. The Dambar Cannot Be Located On The Lower Radius Of The Foot.